Silicon NPN Power Transistors 2SC2810

DESCRIPTION

With TO-220C package

·High voltage,High speed

APPLICATIONS

·For power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

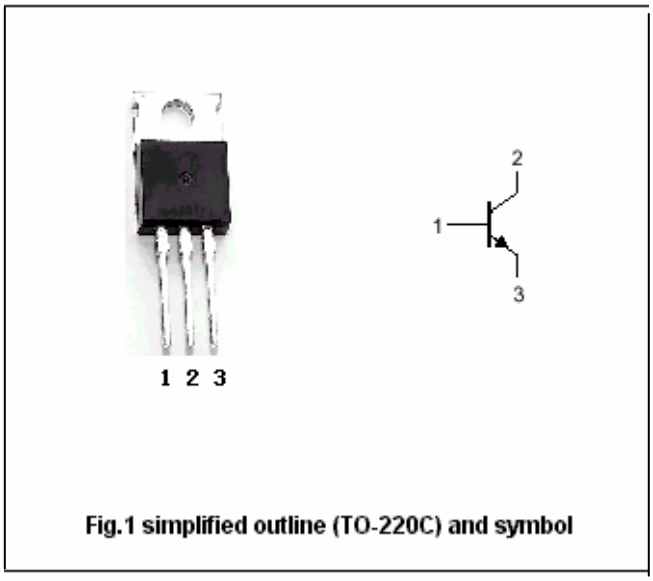


Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		7	A
I_{CM}	Collector current-peak		14	A
P_C	Collector dissipation	T_C=25□	50	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=10mA ; I_B=0	400			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ; I_E=0	500			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ; I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=3A; I_B=0.6A			0.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=3A; I_B=0.6A			1.3	V
I_{CBO}	Collector cut-off current	V_{CB}=500V ;I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=7V; I_C=0			10	μA
h_{FE}	DC current gain	I_C=3A ; V_{CE}=4V	10			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=12V		18		MHz

PACKAGE OUTLINE

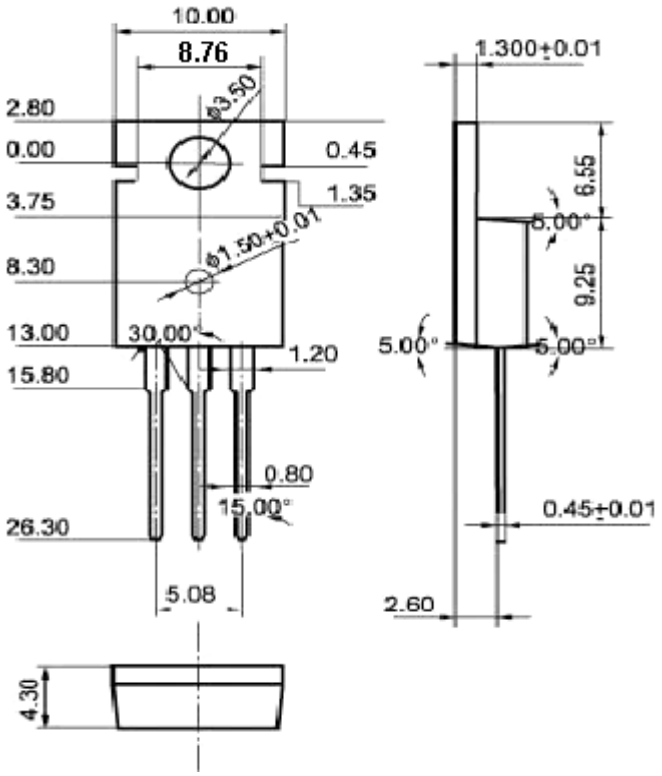


Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)